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AN 1987-196552 [28] WPIDS

DNN N1987-147048 DNC C1987-082359

TI Bonding wire for semiconductor device e.g. IC, LSI - comprises copper contg. sulphur matrix, and indium, magnesium, beryllium, boron, zirconium, silver, silicon, calcium etc..

DC L03 M26 U11 X12

PA (NIHA) NIPPON MINING CO; (TATD) TATSUTA DENSEN KK

CYC 1

PI JP 62127438 A 19870609 (198728) \* 5p JP 03079416 B 19911218 (199203)

ADT JP 62127438 A JP 1985-265621 19851126; JP 03079416 B JP 1985-265621 19851126

PRAI JP 1985-265621 19851126

AB JP 62127438 A UPAB: 19930922

The bonding wire comprises Cu having 99.999

wt.% or over purity, contg. 0.0005 wt.% or less S, as a matrix, to which as additive elements, less than 0.02 wt.% (A) In and Mg, as a total, and 0.01 wt.% or less (B) at least one of Be, B, Zr, Y,

Ag, Si, Ca, and rare earth elements, but 0.02 wt. % or less (A)+(B) groups, are added.

USE - The bonding wire is used for connection between electrodes on semiconductor devices such as transistors, IC's, and LSI's, and outer leads. With the wire, heat resistance, fracture strength and bonding characteristics can be improved.

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